

CLAIMS

- Sub #17
1. A ceramic substrate for a semiconductor-producing/examining device having a conductor formed on a surface of the ceramic substrate or inside the ceramic substrate,
5 wherein:
said substrate is made of a non-oxide ceramic containing oxygen; and
10 the pore diameter of the maximum pore thereof is 50 μ m or less.
2. The ceramic substrate for the semiconductor-producing/examining device according to claim 1,
15 wherein said non-oxide ceramic is a nitride ceramic.
3. The ceramic substrate for the semiconductor-producing/examining device according to claim 1,
20 wherein said non-oxide ceramic is a carbide ceramic.
4. The ceramic substrate for the semiconductor-producing/examining device according to any of claims 1 to 3,
25 wherein said ceramic substrate contains oxygen in an amount of 0.05 to 10% by weight.
- Sub #27
5. The ceramic substrate for the semiconductor-producing/examining device according to any of claims 1 to 4,
30 wherein said ceramic substrate has a porosity of 5% or less.
6. The ceramic substrate for the semiconductor-producing/examining device according to any of
35 claims 1 to 5,
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wherein said ceramic substrate is used within the temperature range of 100 to 700 °C.

7. The ceramic substrate for the
5 semiconductor-producing/examining device according to any of claims 1 to 6,

wherein said ceramic substrate has a thickness of 25 mm or less, and a diameter of 200 mm or more.

- 10 8. The ceramic substrate for the semiconductor-producing/examining device according to any of claims 1 to 7,

wherein said ceramic substrate has a plurality of through holes into which lifter pins for a semiconductor wafer will be
15 inserted.

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